	L #	Hits	Search Text	DBs	Time Stamp
1	L1	110	(("6784072") or ("6404014") or ("6429488") or ("6486037") or ("6602757") or ("6495429") or ("6593205") or ("6812114") or ("6743651") or ("6756639") or ("6835983") or ("6989058") or ("7084460") or ("6888221") or ("7075150") or ("6967376") or ("7067371") or ("7115463") or ("7141457") or ("5188978") or ("5767549") or ("6214694") or ("6255145") or ("6180486") or ("6426252") or ("6566177") or ("6222253") or ("6300218") or ("6432754") or ("7656257") or ("6043166") or ("5930643") or ("6090689") or ("6259137") or ("6204546") or ("6333532") or ("6846727") or ("6541356") or ("6805962") or ("6841457") or ("6946373") or ("6800518") or ("6717217") or ("6855436") or ("7049660") or ("7026249") or ("7169226") or ("7124558") or ("6861158") or ("7074686") or ("6991998") or ("7172930") or ("7141115") or ("7084050")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 09:24
2	L3	43	L1 not L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 09:30
3	L2	67	L1 and ion near (implant$7 bombard$7 inject$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 10:17

10/674,647 & 10/674,648

5/31/2007, EAST Version: 2.1.0.14

	L #	Hits	Search Text	DBs	Time Stamp
4	L4	2	L2 and (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:12
5	L5	2	L3 and (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:19
6	L7	10676	((427/526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:08
7	L8	5312	(SOI GeSOI GSOI GeSiOI GESiOI (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant$7 bombard$7 inject$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:11
8	L9	3919	(Vacancies voids pores porous porosity damag$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dope$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:16
9	L10	66	L8 same L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:17

3

	L #	Hits	Search Text	DBs	Time Stamp
10	L11	199	L8 and L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:17
11	L13	66	L10 and L11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:18
12	L15	133	L11 not L13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:18
13	L16	1904	("HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofloride Hydrofluoricacid hydrofluorideacid Hydro adj (fluoride fluoric floric)) Same (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:26
14	L17	29	L13 and L16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:38
15	L18	36	L15 and L16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39
16	L19	37	L13 not L17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39

4

	L #	Hits	Search Text	DBs	Time Stamp
17	L20	97	L15 not L18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:39
18	L21	1	L17 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:40
19	L22	28	L17 not L21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:40
20	L23	1	L18 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
21	L24	1	L19 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
22	L25	4	L20 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
23	L26	35	L18 not L23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41

Have

has pre pubs (648)

5

	L #	Hits	Search Text	DBs	Time Stamp
24	L27	36 ✓	L19 not L24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:41
25	L28	93	L20 not L25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/05/31 13:42